

<b>SANYO</b>	No.1289C	<b>2SA1347/2SC3401</b>
		PNP/NPN Epitaxial Planar Silicon Transistors <b>Switching Applications</b> (with Bias Resistance)

**Applications**

Switching circuit, inverter, interface circuit, driver

**Features**

- Built-in bias resistor ( $R_1=46k\Omega$ ,  $R_2=23k\Omega$ ).
- Small-sized package (SPA).

( ): 2SA1347

**Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$**

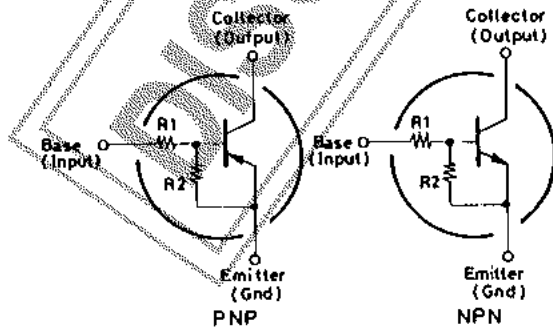
			unit
Collector to Base Voltage	$V_{CBO}$	(-)150	V
Collector to Emitter Voltage	$V_{CEO}$	(-)150	V
Emitter to Base Voltage	$V_{EBO}$	(-)10	V
Collector Current	$I_C$	(-)100	mA
Collector Current(Pulse)	$I_{CP}$	(-)200	mA
Collector Dissipation	$P_C$	300	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics/ $T_a=25^\circ\text{C}$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-)140\text{V}$ , $I_E=0$			(-)0.1	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE}=(-)140\text{V}$ , $I_B=0$			(-)0.5	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-)15\text{V}$ , $I_C=0$	(-)140	(-)172	(-)100	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=(-)15\text{V}$ , $I_C=(-)5\text{mA}$	50			
Gain-bandwidth product	$f_T$	$V_{CE}=(-)10\text{V}$ , $I_C=(-)5\text{mA}$		250 (200)		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=(-)10\text{V}$ , $f=1\text{MHz}$		3.7 (5.5)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)5\text{mA}$ , $I_B=(-)0.25\text{mA}$	(-)0.1	(-)0.3		V

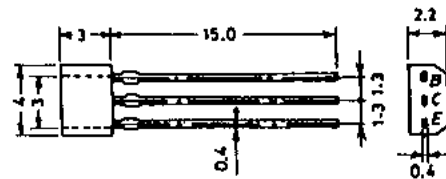
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**Electrical Connection**



**Case Outline 2033**

(unit: mm)



B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

Specifications and information herein are subject to change without notice.

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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)100\mu A, R_{BE} = \infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE} = (-)5V, I_C = (-)100\mu A$	(-)1.2	(-)1.6	(-)2.3	V
Input On Voltage	$V_{I(on)}$	$V_{CE} = (-)0.2V, I_C = (-)15mA$	(-)1.5	(-)3.1	(-)6.0	V
Input Resistance	$R_1$		32	46	60	k $\Omega$
Input Resistance Ratio	$R_1/R_2$		1.8	2.0	2.2	-

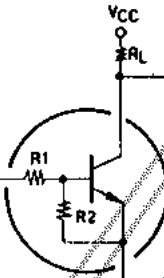
■ Sample Application Circuit

Input ON-state voltage: 6V or more

Input OFF-state voltage: 1.2V or less



INPUT



(For PNP, the polarity is reversed.)

